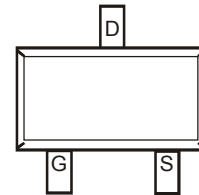
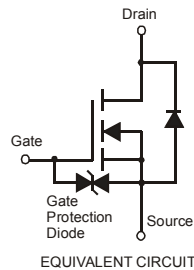


Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 2kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>



TOP VIEW



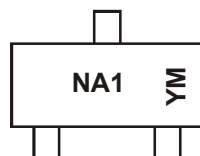
TOP VIEW

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|-------------|--------|--------------------|
| DMG1012UW-7 | SOT323 | 3000 / Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



NA1 = Product Type Marking Code
YM = Date Code Marking
Y or Ȳ = Year (ex: 1 = 2021)
M = Month (ex: 9 = September)

Date Code Key

| Year | 2009 | | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 |
|------|------|-------|------|------|------|------|------|------|------|------|------|------|
| Code | W | | I | J | K | L | M | N | O | P | R | S |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|-----------------------------------|--------------|------------------------|------------------|-------|------|
| Drain-Source Voltage | | | V _{DSS} | 20 | V |
| Gate-Source Voltage | | | V _{GSS} | ±6 | V |
| Continuous Drain Current (Note 5) | Steady State | T _A = +25°C | I _D | 1.0 | A |
| | | T _A = +85°C | | 0.64 | |
| Pulsed Drain Current (Note 6) | | | I _{DM} | 6 | A |

Thermal Characteristics

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------|--------------------|
| Power Dissipation (Note 5) | P_D | 0.29 | W |
| Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5) | $R_{\theta JA}$ | 425 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|--------------|-----|-------|-----------|----------|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 20 | - | - | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$ | I_{DSS} | - | - | 100 | nA | $V_{DS} = 20V, V_{GS} = 0V$ |
| Gate-Source Leakage | I_{GSS} | - | - | ± 1.0 | μA | $V_{GS} = \pm 4.5V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 7) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | 0.5 | - | 1.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | - | 0.3 | 0.45 | Ω | $V_{GS} = 4.5V, I_D = 600mA$ |
| | | | 0.4 | 0.6 | | $V_{GS} = 2.5V, I_D = 500mA$ |
| | | | 0.5 | 0.75 | | $V_{GS} = 1.8V, I_D = 350mA$ |
| | | | | | | |
| Forward Transfer Admittance | $ Y_{fs} $ | - | 1.4 | - | S | $V_{DS} = 10V, I_D = 400mA$ |
| Diode Forward Voltage | V_{SD} | - | 0.7 | 1.2 | V | $V_{GS} = 0V, I_S = 150mA$ |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | C_{iss} | - | 60.67 | - | pF | $V_{DS} = 16V, V_{GS} = 0V, f = 1.0MHz$ |
| Output Capacitance | C_{oss} | - | 9.68 | - | pF | |
| Reverse Transfer Capacitance | C_{rss} | - | 5.37 | - | pF | |
| Total Gate Charge | Q_g | - | 736.6 | - | pC | $V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA$ |
| Gate-Source Charge | Q_{gs} | - | 93.6 | - | pC | |
| Gate-Drain Charge | Q_{gd} | - | 116.6 | - | pC | |
| Turn-On Delay Time | $t_{D(on)}$ | - | 5.1 | - | ns | $V_{DD} = 10V, V_{GS} = 4.5V, R_L = 47\Omega, R_G = 10\Omega, I_D = 200mA$ |
| Turn-On Rise Time | t_R | - | 7.4 | - | ns | |
| Turn-Off Delay Time | $t_{D(off)}$ | - | 26.7 | - | ns | |
| Turn-Off Fall Time | t_F | - | 12.3 | - | ns | |

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

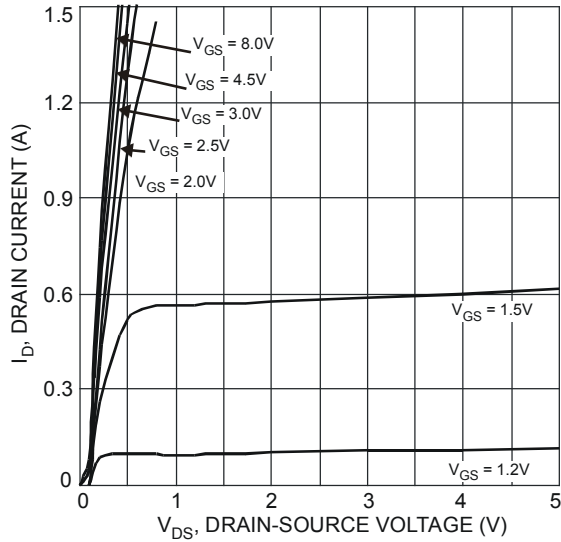


Fig. 1 Typical Output Characteristics

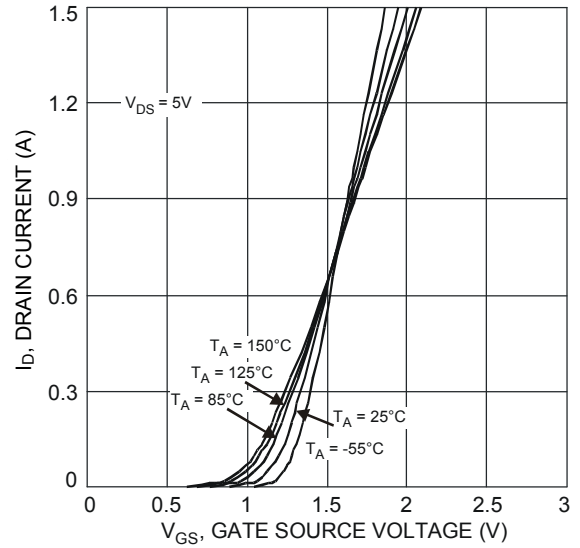


Fig. 2 Typical Transfer Characteristics

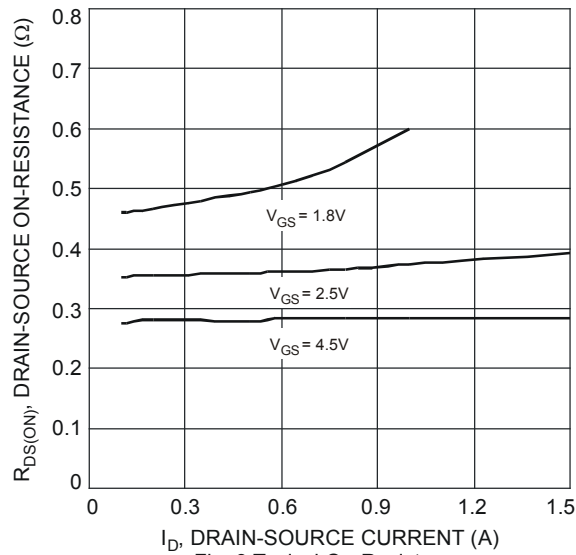


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

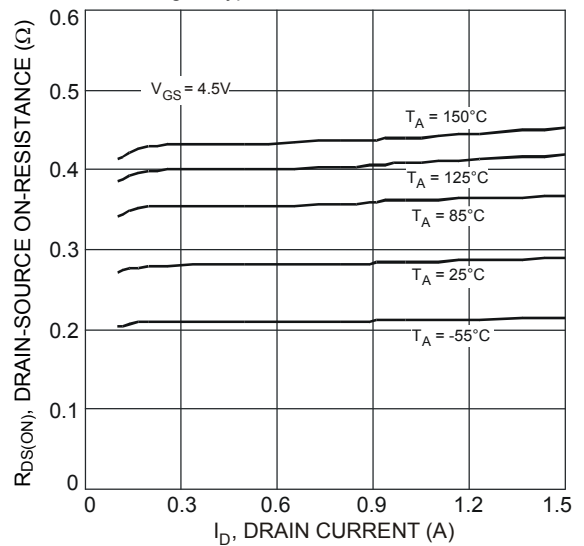


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

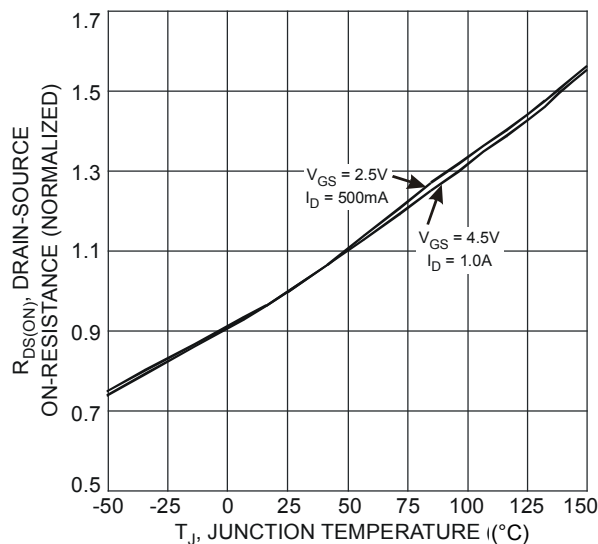


Fig. 5 On-Resistance Variation with Temperature

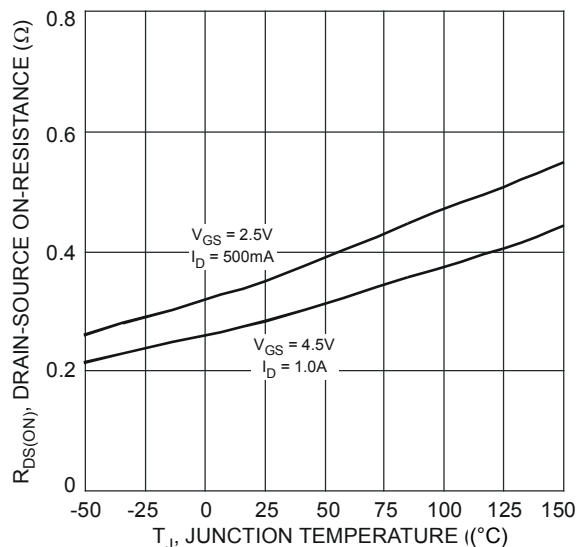


Fig. 6 On-Resistance Variation with Temperature

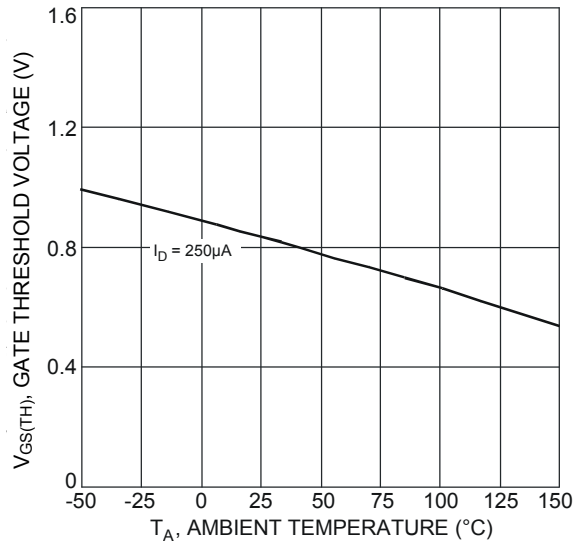


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

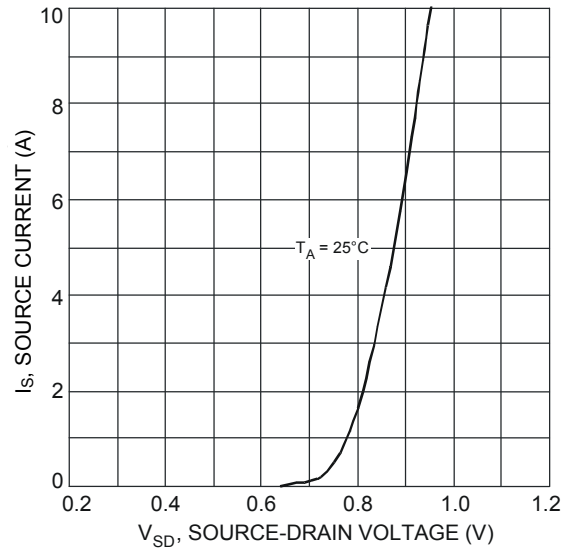


Fig. 8 Diode Forward Voltage vs. Current

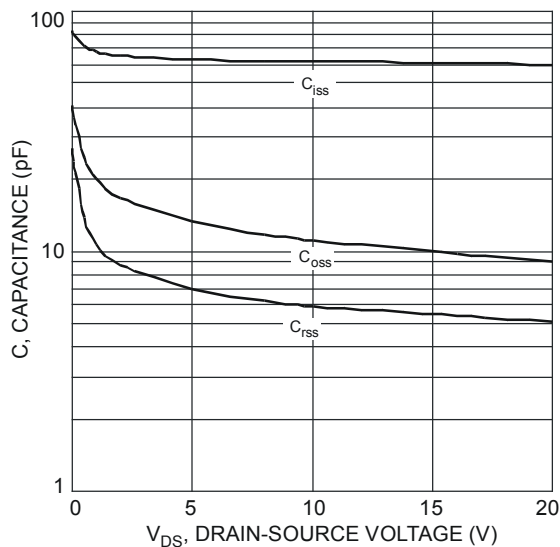


Fig. 9 Typical Capacitance

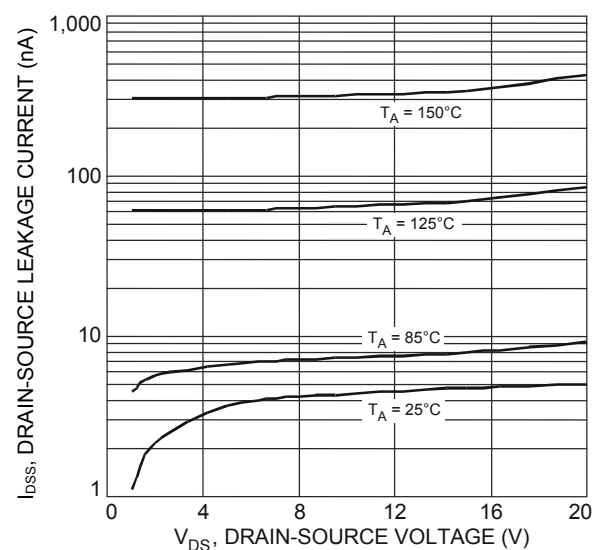


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

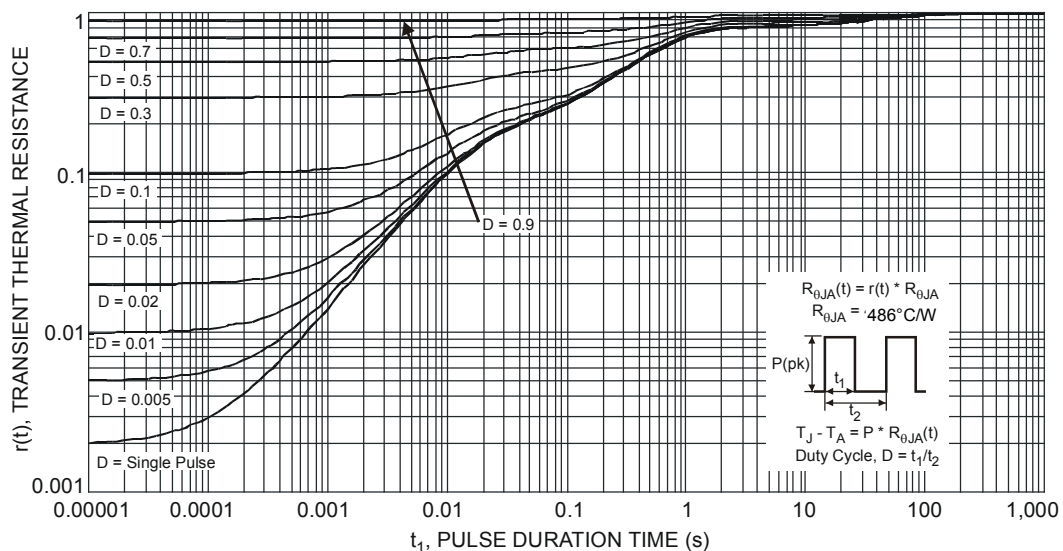
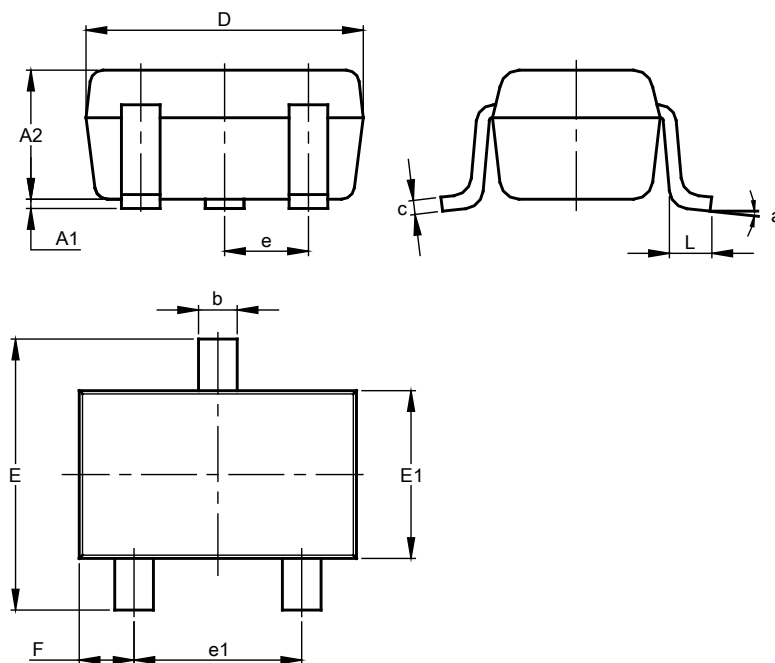


Fig. 11 Transient Thermal Response

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323

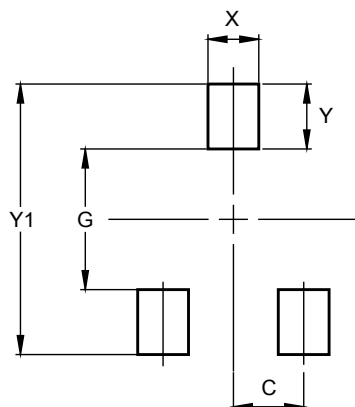


| SOT323 | | | |
|----------------------|------|-------|--------|
| Dim | Min | Max | Typ |
| A1 | 0.00 | 0.10 | 0.05 |
| A2 | 0.80 | 1.00 | 0.90 |
| b | 0.20 | 0.40 | 0.30 |
| c | 0.08 | 0.18 | 0.13 |
| D | 1.80 | 2.20 | 2.00 |
| E | 2.00 | 2.45 | 2.225 |
| E1 | 1.15 | 1.35 | 1.25 |
| e | -- | -- | 0.65 |
| e1 | 1.20 | 1.40 | 1.30 |
| F | 0.25 | 0.475 | 0.3625 |
| L | 0.25 | 0.46 | 0.355 |
| a | 0° | 8° | -- |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.650 |
| G | 1.300 |
| X | 0.470 |
| Y | 0.600 |
| Y1 | 2.500 |

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